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Gaitan et al.

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(54) **POWER SENSOR**

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(51) **Int. Cl.**⁷ **H01L 29/06**

(52) **U.S. Cl.** **257/619; 257/622**

(58) **Field of Search** 257/416, 417, 257/418, 419, 619, 622

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(57) **ABSTRACT**

A method for forming a single cavity in a substrate, which may extend approximately the length of a device located on top of the substrate, and device produced thereby. The device has a length and a width, and may extend approximately the length of the substrate. After locating the device on the surface of the substrate, a first etchant is applied through openings on the surface of the substrate. Subsequently, a second etchant is applied through the same openings on the surface of the substrate. As a result, a single cavity is formed beneath the surface of the device, suspending the device and minimizing electrical coupling.

14 Claims, 8 Drawing Sheets

